

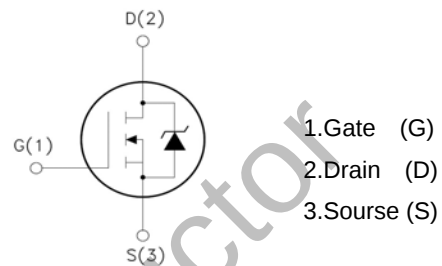
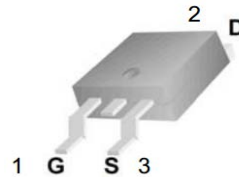
FQD30N06S

60V N-Channel MOSFET

Features:

- ☐ Low Intrinsic Capacitances.
- ☐ Excellent Switching Characteristics.
- ☐ Extended Safe Operating Area.
- ☐ Unrivalled Gate Charge :Qg= 50nC (Typ.).
- ☐ BVDSS=60V, I_D=30A
- ☐ R_{DS(on)} : 0.024Ω (Max) @V_G=10V
- ☐ 100% Avalanche Tested

TO-252

**Absolute Maximum Ratings*** (T_c=25°C Unless otherwise noted)

Symbol	PARAMETER	Value	Unit
V _{DSS}	Drain-Source Voltage	60	V
I _D	Drain Current	T _C =25°C	30
		T _C =100°C	21
V _{GS(TH)}	Gate Threshold Voltage	±20	V
E _{AS}	Single Pulse Avalanche Energy (note1)	72	mJ
I _{AR}	Avalanche Current (note2)	90	A
P _D	Power Dissipation (T _c =25°C)	45	W
T _j	Junction Temperature(MAX)	175	°C
T _{stg}	Storage Temperature	-55~+175	°C
TL	Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	PARAMETER	Typ.	MAX.	Unit
R _{θJC}	Thermal Resistance, Junction to Case	-	3.3	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	-	-	°C/W
R _{θCS}	Thermal Resistance, Case to Sink	-	110	°C/W

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.6	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =30A	-	24	35	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =5A	11	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{ISS}	V _{DS} =15V, V _{GS} =0V, F=1.0MHz	-	590	-	PF
Output Capacitance	C _{OSS}		-	70	-	PF
Reverse Transfer Capacitance	C _{RSS}		-	64	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, I _D =2A, V _{GS} =10V, R _G =3Ω	-	6.0	-	nS
Turn-on Rise Time	t _r		-	6.1	-	nS
Turn-Off Delay Time	t _{d(off)}		-	17	-	nS
Turn-Off Fall Time	t _f		-	3.0	-	nS
Total Gate Charge	Q _g	V _{DS} =30V, I _D =15A, V _{GS} =10V	-	25.3	-	nC
Gate-Source Charge	Q _{gs}		-	4.7	-	nC
Gate-Drain Charge	Q _{gd}		-	6.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =30A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	30	A
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF =30A	-	29.5	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs (Note3)	-	50	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$

Typical Characteristics

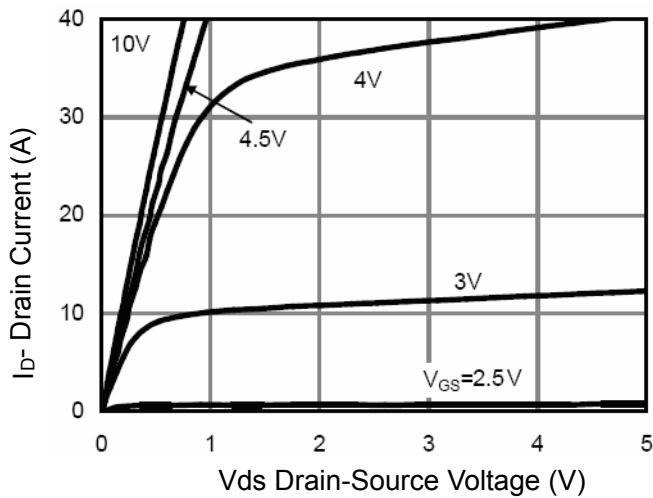


Figure 1 Output Characteristics

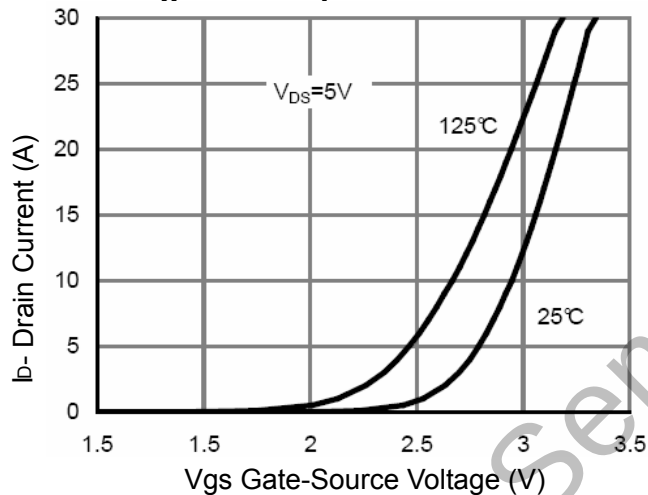


Figure 2 Transfer Characteristics

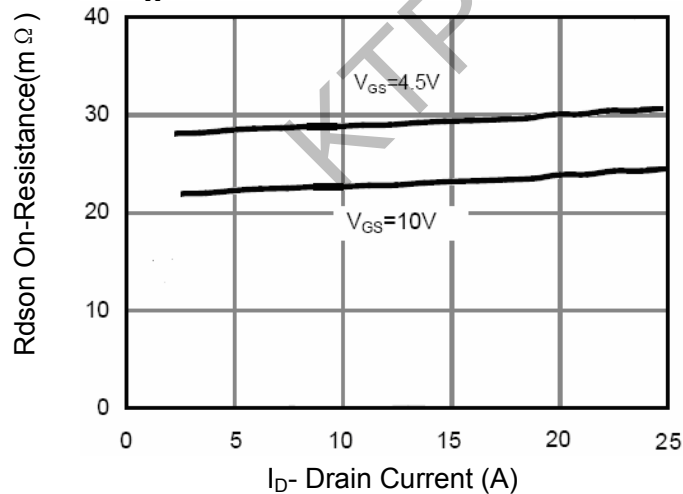


Figure 3 $R_{DS(on)}$ - Drain Current

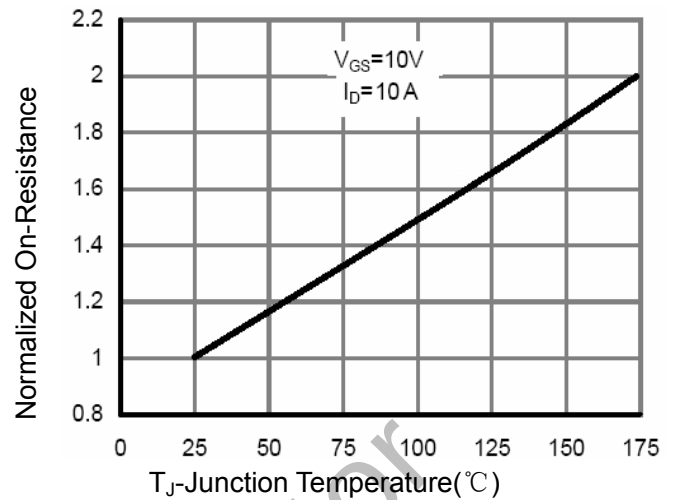


Figure 4 $R_{DS(on)}$ -Junction Temperature

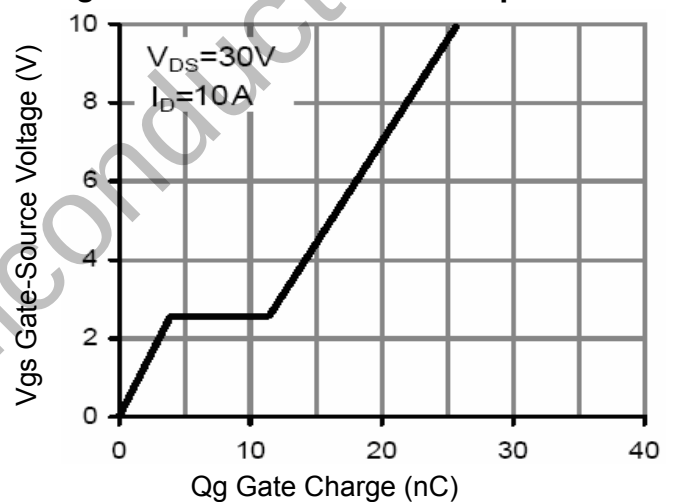


Figure 5 Gate Charge

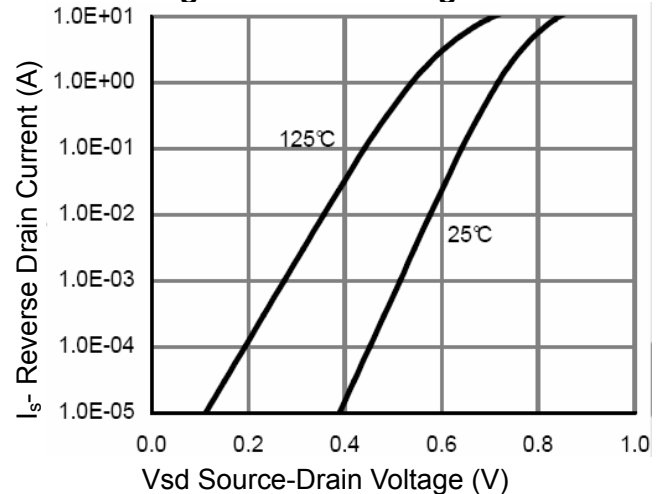


Figure 6 Source- Drain Diode Forward

Typical Characteristics (Continued)

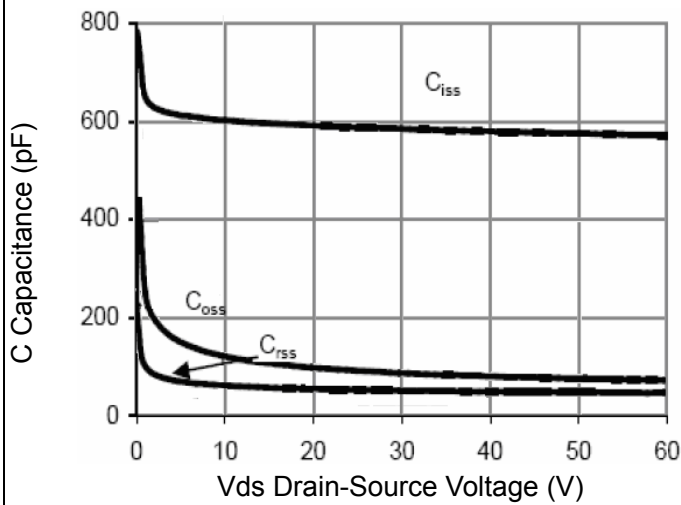


Figure 7 Capacitance vs Vds

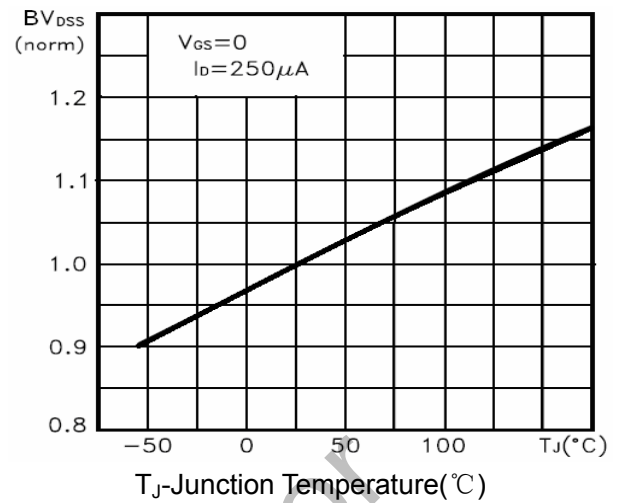


Figure 9 BV_{DSS} vs Junction Temperature

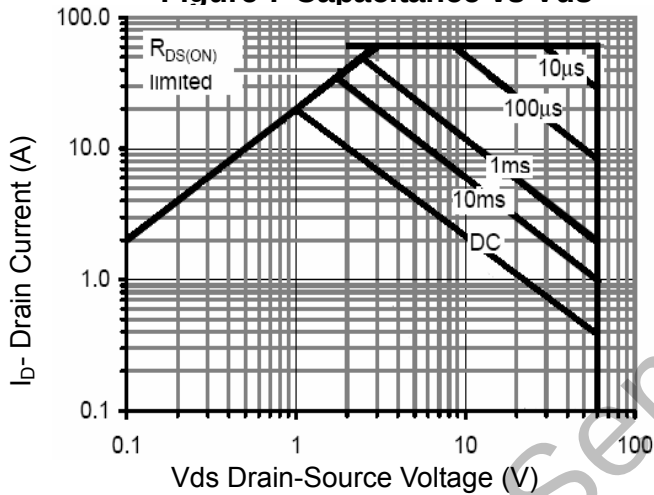


Figure 8 Safe Operation Area

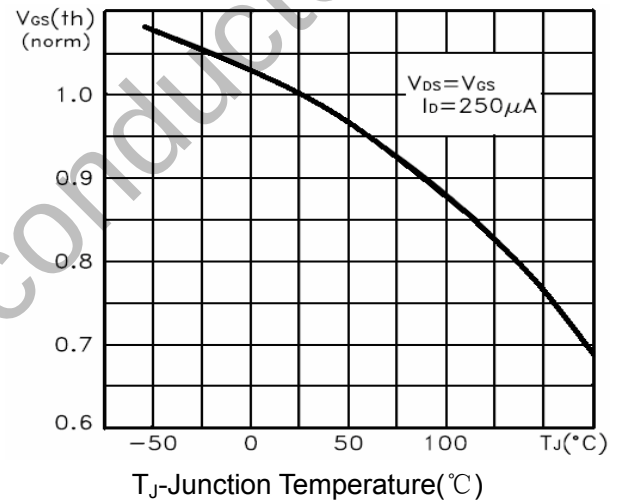


Figure 10 $V_{GS(th)}$ vs Junction Temperature

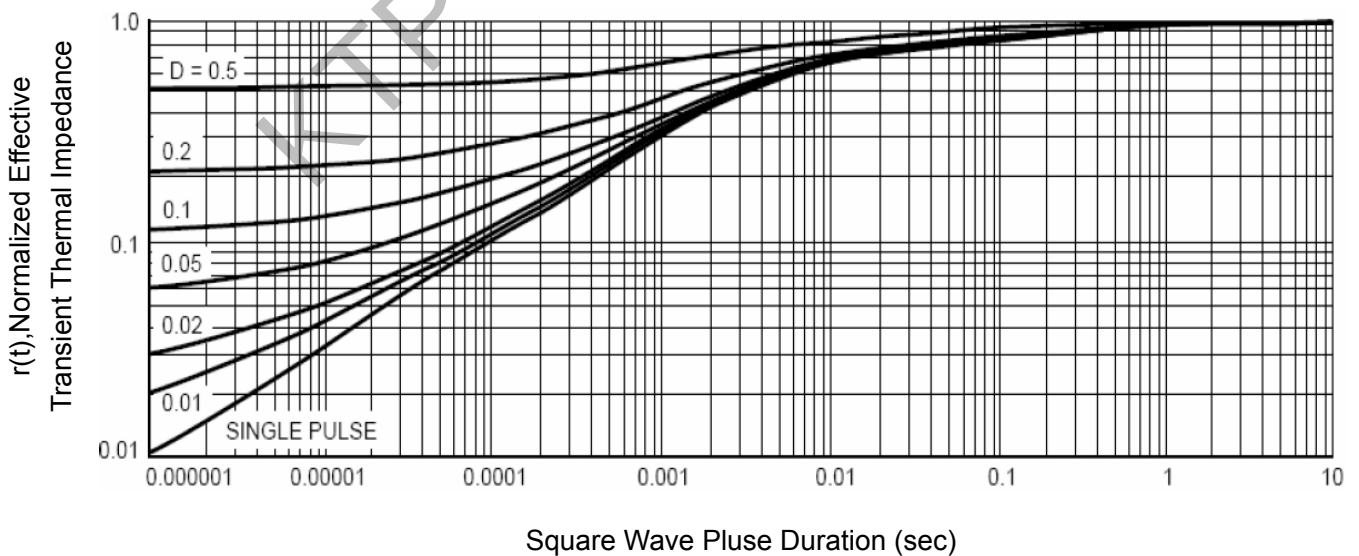
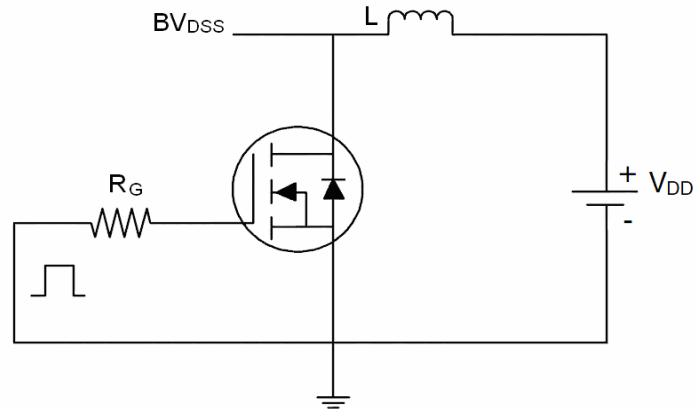


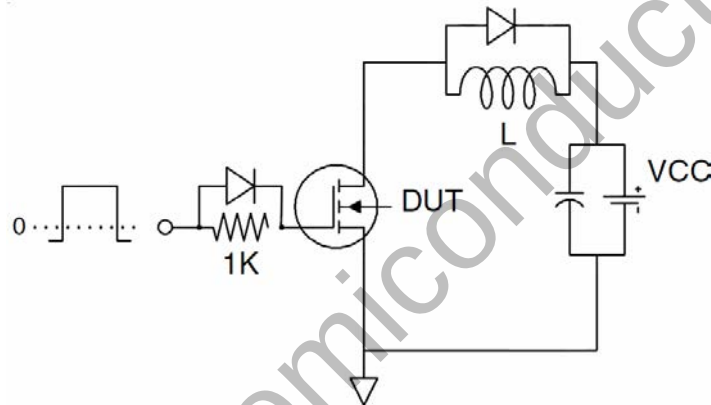
Figure 11 Normalized Maximum Transient Thermal Impedance

Test Circuit

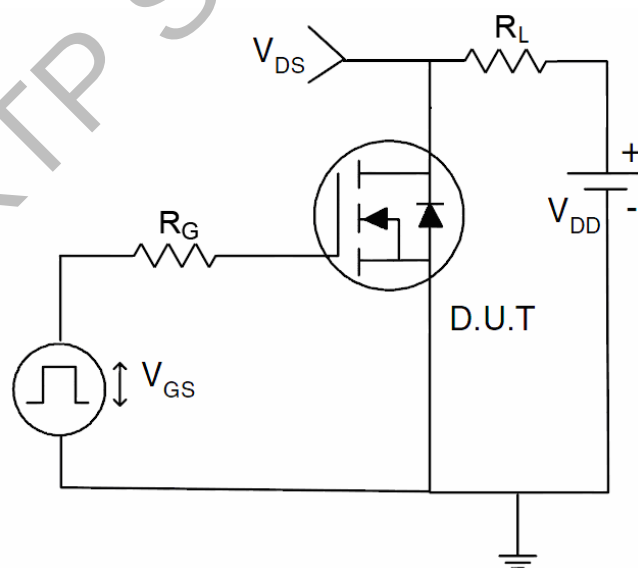
1) E_{AS} test Circuit



2) Gate charge test Circuit



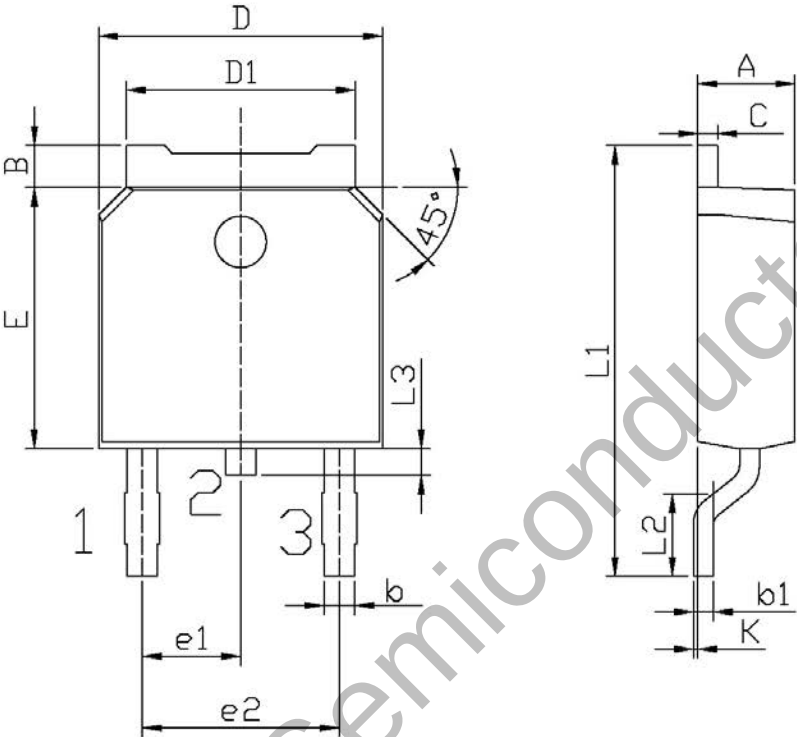
3) Switch Time Test Circuit



Package Dimension

TO-252

Unit:mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	2.20	2.40	E	5.95	6.25
B	0.95	1.25	e1	2.24	2.34
b	0.70	0.90	e2	4.43	4.73
b1	0.45	0.55	L1	9.85	10.35
C	0.45	0.55	L2	1.25	1.75
D	6.45	6.75	L3	0.60	0.90
D1	5.20	5.40	K	0.00	0.10